

2SA1048 PNP Silicon Epitaxial Planar Transistor

for audio frequency amplifier applications.

The transistor is subdivided into three groups, O, Y and G, according to its DC current gain. As complementary type the NPN transistor 2SC2458 is recommended.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	50	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	150	mA
Base Current	$-I_B$	50	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_s	-55 to +125	$^\circ\text{C}$

Characteristics at $T_{amb}=25^{\circ}C$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE}=6V, -I_C=2mA$					
Current Gain Group O	h_{FE}	70	-	140	-
Y	h_{FE}	120	-	240	-
G	h_{FE}	200	-	400	-
Collector Cutoff Current at $-V_{CB}=50V$	$-I_{CBO}$	-	-	0.1	μA
Emitter Cutoff Current at $-V_{EB}=5V$	$-I_{EBO}$	-	-	0.1	μA
Collector Saturation Voltage at $-I_C=100mA, -I_B=10mA$	$-V_{CE(sat)}$	-	0.1	0.3	V
Transition Frequency at $-V_{CE}=10V, -I_C=1mA$	f_T	80	-	-	MHz
Output Capacitance at $-V_{CB}=10V, f=1MHz$	C_{OB}	-	4	7	pF
Noise Figure at $-V_{CE}=6V, -I_C=0.1mA$ $f=1kHz, R_G=10K\Omega$	NF	-	1	10	dB